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YANG et al.(54) **METHOD OF FABRICATING ARRAY
SUBSTRATE, ARRAY SUBSTRATE AND
DISPLAY DEVICE**(71) Applicant: **BOE TECHNOLOGY GROUP CO.,
LTD.**, Beijing (CN)(72) Inventors: **Wei YANG**, Beijing (CN); **Xinhong
LU**, Beijing (CN)(21) Appl. No.: **18/189,569**(22) Filed: **Mar. 24, 2023****Related U.S. Application Data**(63) Continuation of application No. 17/328,393, filed on
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29/7869 (2013.01); *H10K 59/1213* (2023.02)(57) **ABSTRACT**

A display device is disclosed. The display device includes a display area and a wiring area. The display area is disposed with a first thin film transistor which is an oxide thin film transistor and a second thin film transistor which is a low temperature poly-silicon thin film transistor. A distance between a first active layer of the first thin film transistor and a substrate is different from a distance between a second active layer of the second thin film transistor and the substrate. The first thin film transistor includes first vias that receive a first source/drain. The second thin film transistor includes second vias that receives a second source/drain. The wiring area is provided with a groove. The groove includes a first sub-groove and a second sub-groove that are stacked, and depths of the second vias are substantially equal to a depth of the second sub-groove.